Standard specifications of 100 mm Sn-doped β-Ga₂O₃ (001) substrate

	Items	Specifications	
Orientation		(001)	
Dopant		Sn	
Conductivity		n-type	
Nd-Na (cm ⁻³)		$1 \times 10^{18} \sim 2 \times 10^{19}$	
	Diameter (mm)	100 ±0.5	
Dim	Orientation flat width (mm) 32.5 ±2.5		
Dimensions	Index flat width (mm)	18.0 ±2.5	
S	Thickness (mm)	0.65 ±0.02	
	Reference	Fig. 1	
Offset angle (degree)		[010]:0 ±1	
		[100]:0 ±1	
FWHM (arcsec)		[010]:350 or less	
		[100]:350 or less	
Surface	Front	СМР	
	Back	СМР	

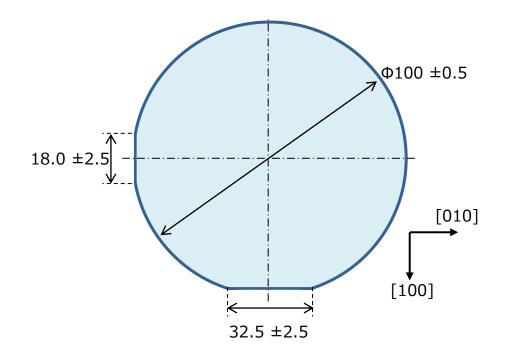


Fig. 1



1 There are cases in which the other side of OF is chipped (a maximum of around IF width). 2 These products must be used for research and development purposes only.

3 The substrates must not be used as a seed crystal.

Remarks

4 The specifications are subject to change without notice.

Standard specifications of 2 inch Sn-doped β-Ga₂O₃ (001) substrate

Items		Specifications	
Orientation		(001)	
Dopant		Sn	
Conductivity		n-type	
Nd-Na (cm ⁻³)		$1 \times 10^{18} \sim 2 \times 10^{19}$	
	Diameter (mm)	50.8 ±0.3	
Dimensions	Orientation flat width (mm)	15.9 ±2.5	
	Index flat width (mm)	8.0 ±2.5	
Ŋ	Thickness (mm) 0.65 ± 0.02		
	Reference	Fig. 2	
Offset angle (degree)		$[010]:0 \pm 1$	
		[100]:0 ±1	
FWHM (arcsec)		[010]:350 or less	
		[100]:350 or less	
Surface	Front	СМР	
	Back	СМР	

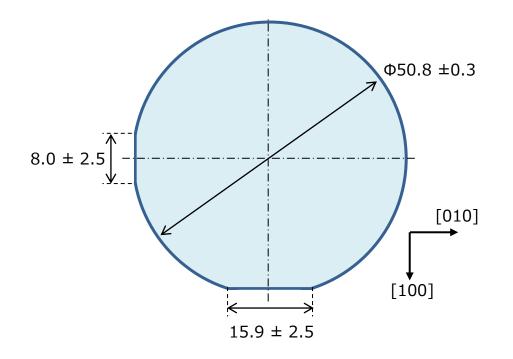


Fig.2



1 There are cases in which the other side of OF is chipped (a maximum of around IF width). 2 These products must be used for research and development purposes only.

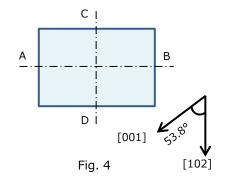
3 The substrates must not be used as a seed crystal.

Remarks

4 The specifications are subject to change without notice.

Standard specifications of 10×15 mm² β-Ga₂O₃ (010) substrates

Items		Specifications			
Orientation		(010)			
Dopant		Sn	Undoped	Fe	
Conductivity		n-type	n-type	Insulating $(>10^{10}\Omega\cdot { m cm})$	
No	d-Na (cm ⁻³)	$1 \times 10^{18} \sim 9 \times 10^{18}$	≦9×10 ¹⁷	-	
D	A-B (mm)	15 ±0.3	15 ±0.3	15 ±0.3	
ime	C-D (mm)	10 ±0.3	10 ±0.3	10 ±0.3	
Dimensions	Thickness (mm)	0.5 ±0.02	0.5 ±0.02	0.5 ±0.02	
SUC	Reference	Fig. 4	Fig. 4	Fig. 4	
Of	fset angle	⊥[102]:0 ±1	⊥[102]:0 ±1	⊥[102]:0 ±1	
(degree)		[102]:0 ±1	$[102]:0 \pm 1$	$[102]:0 \pm 1$	
FWHM (arcsec)		⊥[102]:150 or less	⊥[102]:150 or less	⊥[102]:150 or less	
1 V	villy (arcsec)	[102]:150 or less	[102]:150 or less	[102]:150 or less	
Surface	Front	CMP	CMP	СМР	
	Back	Grinding	Grinding	Grinding	



Remarks



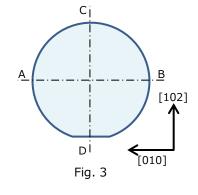
¹ These products must be used for research and development purposes only.

² The substrates must not be used as a seed crystal.

³ The specifications are subject to change without notice.

Standard specifications of 2 inch β -Ga₂O₃ ($\bar{2}$ 01) substrates

Items		Specifications			
Orientation		(201)			
Dopant		Sn	Undoped	Fe	
Conductivity		n-type	n-type	Insulating $(>10^{10}\Omega\cdot cm)$	
No	d-Na (cm ⁻³)	$1 \times 10^{18} \sim 2 \times 10^{19}$	≦9×10 ¹⁷	-	
D	A-B (mm)	50.8 ±0.3	50.8 ±0.3	50.8 ±0.3	
ime	C-D (mm)	49.5 ±0.3	49.5 ±0.3	49.5 ±0.3	
Dimensions	Thickness (mm)	0.68 ±0.02	0.68 ±0.02	0.68 ±0.02	
	Reference	Fig. 3	Fig. 3	Fig. 3	
Of	set angle	[010]: 0 ±0.4	[010]: 0 ±0.4	$[010]:0 \pm 1$	
(d	egree)	[102]:-0.7 ±0.4	[102]:-0.7 ±0.4	[102]:-0.7 ±1	
ΕV	VHM (arcsec)	[010]:150 or less	[010]:150 or less	[010]:150 or less	
1 V	viili (arcsec)	[102]:150 or less	[102]:150 or less	[102]:150 or less	
Surface	Front	CMP	CMP	СМР	
	Back	Grinding	Grinding	Grinding	



Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.

